#### PATENT COOPERATION TREATY

TRANSLATION From the INTERNATIONAL SEARCHING AUTHORITY To: WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY (PCT Rule 43bis.1) Date of mailing (day/month/year) Applicant's or agent's file reference FOR FURTHER ACTION P01-04088WO See paragraph 2 below International filing date (day/month/year) Priority date (day/month/year) International application No. 14.01.2005 19.01.2004 PCT/JP2005/000349 International Patent Classification (IPC) or both national classification and IPC Applicant PIONEER CORPORATION This opinion contains indications relating to the following items: Box No. I Basis of the opinion Box No. II **Priority** Non-establishment of opinion with regard to novelty, inventive step and industrial applicability Box No. III Box No. IV Lack of unity of invention Reasoned statement under Rule 43bis.1(a)(i) with regard to novelty, inventive step or industrial Box No. V applicability; citations and explanations supporting such statement Box No. VI Certain documents cited Certain defects in the international application Box No. VII Box No. VIII Certain observations on the international application 2. **FURTHER ACTION** If a demand for international preliminary examination is made, this opinion will be considered to be a written opinion of the International Preliminary Examining Authority ("IPEA") except that this does not apply where the applicant chooses an Authority other than this one to be the IPEA and the chosen IPEA has notified the International Bureau under Rule 66.1bis(b) that written opinions of this International Searching Authority will not be so considered. If this opinion is, as provided above, considered to be a written opinion of the IPEA, the applicant is invited to submit to the IPEA a written reply together, where appropriate, with amendments, before the expiration of 3 months from the date of mailing of Form PCI/ISA/220 or before the expiration of 22 months from the priority date, whichever expires later. For further options, see Form PCT/ISA/220. For further details, see notes to Form PCT/ISA/220. 3. Authorized officer Name and mailing address of the ISAJP

Telephone No.

Facsimile No.

Box	No. I	Basis of this opinion
1.		regard to the language, this opinion has been established on the basis of the international application in the language in which it was unless otherwise indicated under this item.
•		This opinion has been established on the basis of a translation from the original language into the following language, which is the language of a translation furnished for the purposes of international search (under
	_	Rule 12.3 and 23.1(b)).
2.		regard to any nucleotide and/or amino acid sequence disclosed in the international application and necessary to the claimed ation, this opinion has been established on the basis of:
	a.	type of material
		a sequence listing
		table(s) related to the sequence listing
	<b>b</b> .	format of material
		in written format
•		in computer readable form
	c.	time of filing/furnishing
	•	contained in the international application as filed.
		filed together with the international application in computer readable form.
		furnished subsequently to this Authority for the purposes of search.
3.		In addition, in the case that more than one version or copy of a sequence listing and/or table(s) relating thereto has been filed or furnished, the required statements that the information in the subsequent or additional copies is identical to that in the application as filed or does not go beyond the application as filed, as appropriate, were furnished.
4.	Addi	tional comments:
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Statement   Novelty (N)   Claims   1-6   NC	Box			lc 43bis.1(a)(i) with regar porting such statement	ed to novelty, invent	ive step or industi	rial applicability;
Inventive step (IS)  Claims  Claims  1-6  Industrial applicability (IA)  Claims  1-6  Industrial applicability (IA)  Claims  1-6  Claims  1-6  No  Claims  1-6  No  Claims  1-6  No  Claims  1-6  Claims  No  Claims  Claims  Claims  1-6  No  Claims  1-6  No  Claims  No  Claims  Claims  No  Claims  Claims  Claims  Claims  Document 1: JP, 2003-288983, A (Semiconductor Energy Laboratory Co., Ltd.), 10 October, 2003 (10.10.03), claims 3 and 4, paragraphs [0071], [0072] and [0209]  Document 2: JP, 11-26155. A (Mitsui Chemicals Inc.), 29 January, 1999 (29.01.99), claim 1, paragraphs [0012] and [0013]  Claims 1-6  The above-listed document 1 cited in the ISR describes in the sections indicated above a feature wherein a thin film of silicon oxide nitride, etc., formed by making an organic-compound layer actively taking in hydrogen is created by means of, e.g., plasma CVD in order to prevent the deterioration of the said organic-compound layer.  Accordingly the specification for hydrogen content in terms of the number value in the invention of the present application does not appear to involve an inventive step in view of the above-mentioned description.  Claims 1-6  The above-listed document 2 cited in the ISR describes in the sections indicated above a protective film for an electroluminescence device made by forming a diamond-like carbon film with a hydrogen concentration of not more than 50 atom%.  Accordingly the invention of the present application does not appear to be novel or involve an inventive step in view of the above-mentioned description.	1.						
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Inventive step (IS)  Claims  Claims  1-6  Industrial applicability (IA)  Claims  Claim				1-6	·		
Industrial applicability (IA)  Claims  1-6  No  Claims  1-6  Claims  1-6  Claims  1-6  Claims  1-6  Claims  1-7  Claims  1-7  Claims  1-7  Claims  1-7  Claims  1-7  Claims  1-8  Claims  1-8  Claims  1-8  Claims  1-8  Claims  1-9  Claims  1-9  Claims  1-6  The above-listed document 1 cited in the ISR describes in the sections indicated above a feature wherein a thin film of silicon oxide nitride, etc., formed by making an organic-compound layer actively taking in hydrogen is created by means of, e.g., plasma CVD in order to prevent the deterioration of the said organic-compound layer.  Accordingly the specification for hydrogen content in terms of the number value in the invention of the present application does not appear to involve an inventive step in view of the above-mentioned description.  Claims 1-6  The above-listed document 2 cited in the ISR describes in the sections indicated above a protective film for an electroluminescence device made by forming a diamond-like carbon film with a hydrogen concentration of not more than 50 atom%.  Accordingly the invention of the present application does not appear to be novel or involve an inventive step in view of the above-mentioned description.			Clamb				•••
Industrial applicability (IA)  Claims  Claims  1-6  Claims  1-7  Claims  1-7  Claims  1-7  Claims  1-8  Claim		Inventive step (IS)	Claims	··	<u> </u>		YI
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		Claims 1-6 The above-list feature wherein a thin layer actively taking in deterioration of the said Accordingly the invention of the present above-mentioned description.  Claims 1-6 The above-list protective film for an early a hydrogen concentration of the present above-description.	ed docume film of silication hydrogen d organic- ne specification at application ed docume electrolumion of not ne invention	nt 1 cited in the ISF con oxide nitride, et is created by means compound layer ation for hydrogen con on does not appear to the scence device man of the present app	describes in the content in terms to involve an inde by forming dication does not be content in the content in terms to involve and inde by forming dication does not be content in the co	ne sections inconsting an orgonal CVD in order of the number ventive step in a diamond-like	dicated above a anic-compound er to prevent the er value in the n view of the dicated above a see carbon film with
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	R	de 12.3 and 23.1(b)).	
2.		gard to any nucleotide and/or amino acid sequence disclosed in the international application and necessary to the claims in this opinion has been established on the basis of:	:d
•	a. t	ce of material	
··		a sequence listing	
		table(s) related to the sequence listing	
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	<u> </u>	in written format	
		in computer readable form	
	c. ti	ne of filing/furnishing	
		contained in the international application as filed.	
	Γ	filed together with the international application in computer readable form.	,
	Ē	furnished subsequently to this Authority for the purposes of search.	
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4.	Additio	nal comments:	
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Claims 1-6  Inventive step (IS)  Claims	Indu  Citation  Docu (10.10  Docu parag  Claim featur layer deteri inven above  Claim  protee		anations sur		•	novery, inventive.	sich or industria	l applicability;
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Inventive step (IS)  Claims  Claims  Claims  Claims  Claims  Claims  Claims  1-6  Industrial applicability (IA)  Claims  Claims  Claims  1-6  Y  Claims  Claims  Claims  Claims  1-6  Y  Claims  Claims  Claims  Claims  Claims  Claims  Claims  1-6  Y  Claims  N  Claims  Claims  Claims  Claims  Claims  Claims  1-6  Y  Claims  Claims  N  Claims  Claims  A (Semiconductor Energy Laboratory Co., Ltd.), 10 October, 2003 (10.10.03), claims 3 and 4, paragraphs [0071], [0072] and [0209]  Document 2: JP, 11-26155, A (Mitsui Chemicals Inc.), 29 January, 1999 (29.01.99), claim 1, paragraphs [0012] and [0013]  Claims 1-6  The above-listed document 1 cited in the ISR describes in the sections indicated above a feature wherein a thin film of silicon oxide nitride, etc., formed by making an organic-compound layer actively taking in hydrogen is created by means of, e.g., plasma CVD in order to prevent the deterioration of the said organic-compound layer.  Accordingly the specification for hydrogen content in terms of the number value in the invention of the present application does not appear to involve an inventive step in view of the above-mentioned description.  Claims 1-6  The above-listed document 2 cited in the ISR describes in the sections indicated above a protective film for an electroluminescence device made by forming a diamond-like carbon film with a hydrogen concentration of not more than 50 atom%.	Indu  Citation  Docu (10.10  Docu parag  Claim  featur layer deteri  inven above  Claim  protect a hyd					•		
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